

Chiral smectic transition phases appearing near the electric field-induced phase transition observed by resonant micro-beam X-ray scattering

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1 Introduction

Chiral smectic (tilted) C liquid crystals are characterized by a one-dimensional layer structure and an average molecular orientation tilted from the layer normal. Various sub-phases in the chiral smectic C phases are classified by the q_T number, where $q_T = [F]/([F] + [A])$ and $[F]$ and $[A]$ are the numbers of synclinal and anticlinal orderings in a unit periodicity, respectively; the ferroelectric phase $\text{SmC}^*(q_T=1)$ and the anti-ferroelectric phase ($\text{SmC}_A^*(q_T=0)$). The close relation between the temperature and electric-field induced phase transition has been shown and the electric field vs. temperature (E - T) phase diagram has been studied [1]. The chiral smectic intermediate phase appearing under the electric field is important for revealing a phase transition mechanism of the successive phase transition. For the smectic phase identification, resonant X-ray scattering (RXS) has been the most powerful technique [2].

In the previous report [3], a new long range order sub-phase appearing between the ferroelectric and the ferroelectric phases in the Br contained liquid crystal was reported. In this report [4], the experiments were carried out at higher temperature range to confirm the long range new transition phase. An X-ray intensity analysis based on the Ising model was also performed.

2 Experiment

The Br contained liquid crystal used was the (*S,S*)-bis-[4'-(1-methylheptyloxycarbonyl)-4-biphenyl] 2-bromoterephthalate and is sandwiched between 80 μm thick glass plates coated with indium tin oxide as an electrode. The phase sequence of the material is Iso 201.3°C SmA 155°C $\text{SmC}\alpha^*$ 151.5°C SmC^* 147°C $\text{SmC}_A^*(q_T=1/2)$ 145°C $\text{SmC}_A^*(q_T=1/3)$ 142°C $\text{SmC}_A^*(q_T=0)$. The detailed characterization of this new chiral smectic liquid crystal was reported previously [2]. The applied electric field was a square wave form with 20Hz.

Resonant X-ray scattering (RXS) experiments were performed on the beam line 4A using a KB focusing system. The incident energy was set at the absorption edge of Br (13.48 keV) and the beam size was about 5 x 5 μm^2 . A pixel array detector (Pilatus-100K, DECTRIS) located at 80 cm from the sample (focusing point) was used for the measurement.

3 Results and Discussion

At 144°C, $m/3$ -order ($m=1$ and 2) reflections appeared below ± 26.5 V (Fig.1(a)).

Near the phase boundary between three-layer periodicity and ferroelectric phases, the RXS diffraction pattern exhibited the spotty streak pattern (Fig. 1(b)). At 145.2°C (assigned as $\text{SmC}_A^*(q_T=1/2)$), between ± 18 V and ± 20 V, there first appeared the spotty reflection between the $m/3$ -order reflections and the layer reflection, and then a weak streak remained at ± 22 V.

Detailed measurements near the phase boundary between three-layer periodicity and ferroelectric phases, the 12-layer periodicity transition phase was confirmed. An X-ray intensity analysis based on the Ising model suggested that the 12-layer periodicity phase was composed of two 3-layer ferroelectric blocks and six synclinal layers (Fig.2).

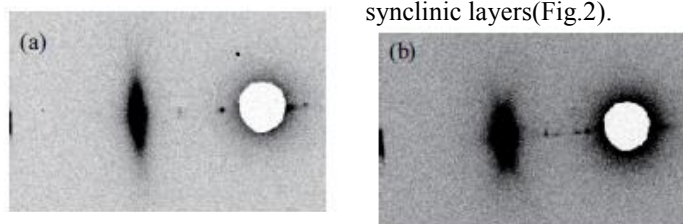


Fig. 1 RXS patterns at applied fields of (a) 0 V and (b) ± 26.5 V at 144 °C.

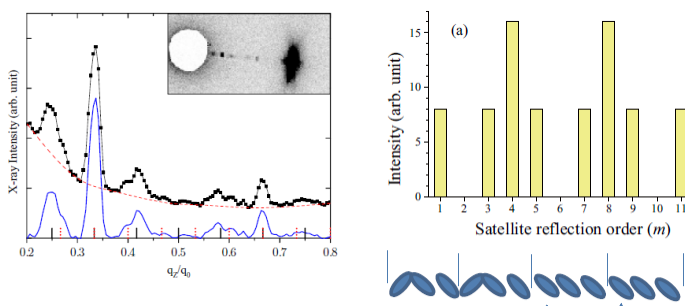


Fig.2 (left) The intensity distribution along the layer normal as a function of the normalized scattering vector. (right) Calculated RXS satellite intensities for the 12-layer periodicities shown in the lower panels.

References

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